

CMKD4448
SURFACE MOUNT
ULTRAmi™
TRIPLE ISOLATED
HIGH SPEED
SILICON SWITCHING DIODES



Central™

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKD4448 type contains three (3) Isolated High Speed Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in an ULTRAmi™ surface mount package, designed for applications requiring high speed switching applications.

MARKING CODE: K48

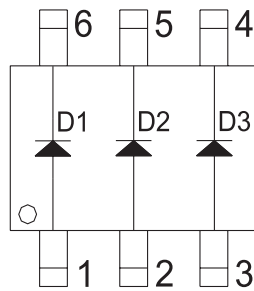
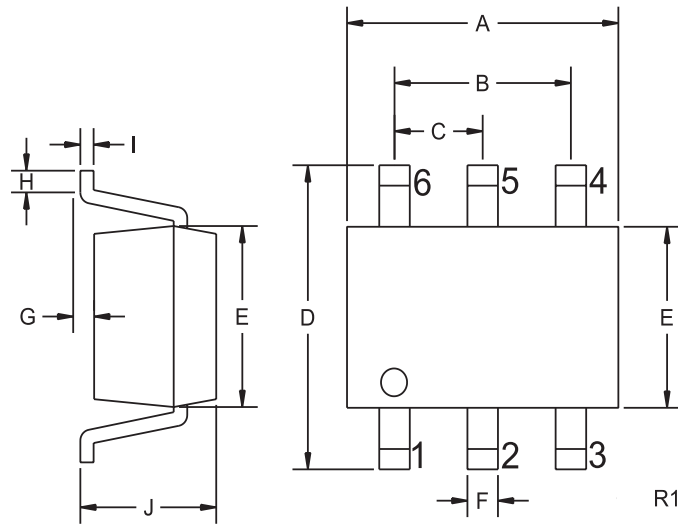
MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	75	V
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Continuous Forward Current	I_F	250	mA
Peak Repetitive Forward Current	I_{FRM}	250	mA
Forward Surge Current, $t_p=1 \mu\text{sec}$.	I_{FSM}	4000	mA
Forward Surge Current, $t_p=1 \text{ sec}$.	I_{FSM}	1000	mA
Power Dissipation	P_D	250	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	500	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=20\text{V}$		25	nA
BV_R	$I_R=5.0\mu\text{A}$	75		V
BV_R	$I_R=100\mu\text{A}$	100		V
V_F	$I_F=100\text{mA}$		1.0	V
C_T	$V_R=0, f=1 \text{ MHz}$		4.0	pF
t_{rr}	$I_R=I_F=10\text{mA}, R_L=100\Omega \text{ Rec. to } 1.0\text{mA}$		4.0	ns

SOT-363 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) ANODE 1
- 2) ANODE 2
- 3) ANODE 3
- 4) CATHODE 3
- 5) CATHODE 2
- 6) CATHODE 1

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.073	0.085	1.85	2.15
B	0.051		1.30	
C	0.026		0.65	
D	0.075	0.091	1.90	2.30
E	0.043	0.055	1.10	1.40
F	0.006	0.012	0.15	0.30
G	0.000	0.004	0.00	0.10
H	0.010	-	0.25	-
I	0.004	0.010	0.10	0.25
J	0.031	0.039	0.80	1.00

SOT-363 (REV: R1)

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R1 (13-November 2002)